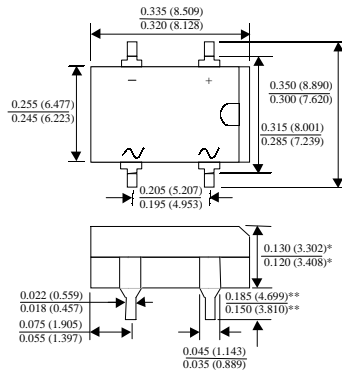


DF005M - DF10M

Features

- Surge overload rating: 50 amperes peak.
- Glass passivated junction.
- Low leakage.



LOW PROFILE ALSO AVAILABLE
 BODY - - 0.102 (2.591)**
 0.095 (2.413)**
 LEAD - - 0.080 (2.032)**
 0.050 (1.270)**

DIP

1.5 Ampere Bridge Rectifiers

Absolute Maximum Ratings* $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
I_O	Average Rectified Current @ $T_A = 40^\circ\text{C}$	1.5	A
$i_f(\text{surge})$	Peak Forward Surge Current 8.3 ms single half-sine-wave Superimposed on rated load (JEDEC method)	50	A
P_D	Total Device Dissipation Derate above 25°C	3.1 25	W mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient,** per leg	40	$^\circ\text{C}/\text{W}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

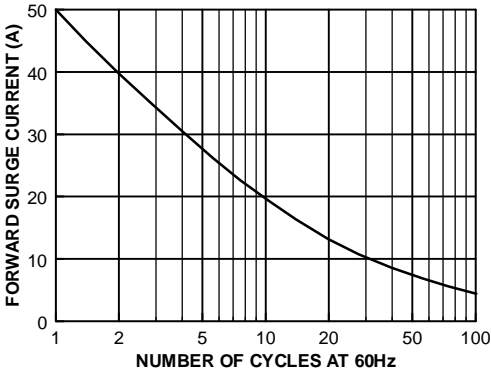
**Device mounted on PCB with $0.5 \times 0.5"$ ($13 \times 13 \text{ mm}$).

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

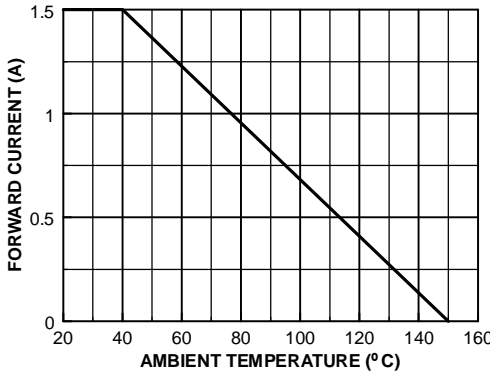
Parameter	Device							Units
	005M	01M	02M	04M	06M	08M	10M	
Peak Repetitive Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Bridge Input Voltage	35	70	140	280	420	560	700	V
DC Reverse Voltage (Rated V_R)	50	100	200	400	600	800	1000	V
Maximum Reverse Leakage, total bridge @ rated V_R $T_A = 25^\circ\text{C}$	5.0							μA
$T_A = 125^\circ\text{C}$	500							μA
Maximum Forward Voltage Drop, per bridge @ 1.0 A	1.1							V
I^2t rating for fusing $t < 8.35 \text{ ms}$	10							A^2Sec
Typical Junction Capacitance, per leg $V_R = 4.0 \text{ V}$, $f = 1.0 \text{ MHz}$	25							pF

Typical Characteristics

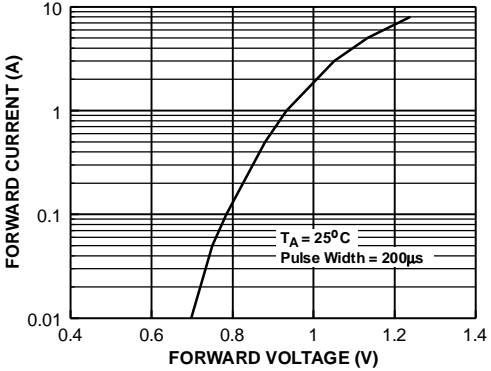
Non-Repetitive Surge Current



Output Rectified Current



Forward Characteristics



Reverse Characteristics

